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	HIT1P077/	Unassigned
	HSJ920040021US1	
	Applicant:	
	D. Heim et al.	
	Filing Date:	Group Art Unit:
	Herewith	Unassigned

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
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Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
/JM/	14	9526547	1995-10-05	WO	G11B	5/00		
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Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
/JM/	21	"Method of Making Submicron Channel MOSFET", IBM Technical Disclosure Bulletin, pp 3407-3408, December 1981
Examiner /John McPherson/		Date Considered 05/22/2007

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.